250 V, 40 A SWITCHMODE™ Schottky Power Rectifier

Features

- 250 V Blocking Voltage
- Low Forward Voltage Drop, $V_F = 0.86 V$
- Soft Recovery Characteristic, $T_{RR} < 35$ ns
- Stable Switching Performance Over Temperature
- Pb-Free Packages are Available*

Benefits

- Reduces or Eliminates Reverse Recovery Oscillations
- Minimizes Need for EMI Filtering
- Reduces Switching Losses
- Improved Efficiency

Applications

- Power Supply
- Power Management
- Automotive
- Instrumentation

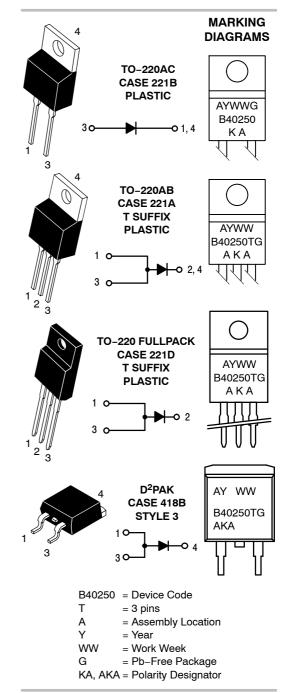
Mechanical Characteristics

- Case: Epoxy, Molded
- Weight: 1.9 grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Epoxy Meets UL 94 V-0 at 0.125 in



ON Semiconductor®

http://onsemi.com



ORDERING INFORMATION

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	250	V
Average Rectified Forward Current (Rated V _R) T _C = 82°C MBR40250, MBR40250T, MBRB40250T (Rated V _R) T _C = 46°C MBRF40250T	I _{F(AV)}	40	A
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz) T _C = 82°C MBR40250, MBR40250T, MBRB40250T (Rated V _R , Square Wave, 20 kHz) T _C = 46°C MBRF40250T	I _{FRM}	80	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I _{FSM}	150	A
Storage Temperature	T _{stg}	- 65 to +175	°C
Operating Junction Temperature	Т _Ј	- 65 to +150	°C
Voltage Rate of Change (Rated V _R)	dv/dt	10,000	V/μs

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Rat	Symbol	Value	Unit	
Maximum Thermal Resistance	Junction-to-Case MBR40250(T) and MBRB40250T MBRF40250 Junction-to-Ambient MBR40250(T) MBRF40250 MBRB40250T	R _{θJC} R _{θJA}	2.0 3.0 60 50 50	°C/W

ELECTRICAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 1) $I_F = 20 \text{ A}, T_C \\ I_F = 20 \text{ A}, T_C \\ I_F = 40 \text{ A}, T_C \\ I_F = 40 \text{ A}, T_C $	= 125°C c = 25°C	0.86 0.71 0.97 0.86	V
Maximum Instantaneous Reverse Current (Note 1) Rated DC Voltage, T _C Rated DC Voltage, T _C	c = 25°C = 125°C	0.25 30	mA
Maximum Reverse Recovery Time $I_F = 1.0 \text{ A}, di/dt = 50 \text{ A}/\mu\text{s}, T_C$	_C = 25°C	35	ns
DYNAMIC CHARACTERISTICS			
Capacitance $V_R = -5.0 \text{ V}, T_C = 25^{\circ}\text{C}, \text{ Frequency} = 10^{\circ}\text{C}$	1.0 MHz C _T	500	pF

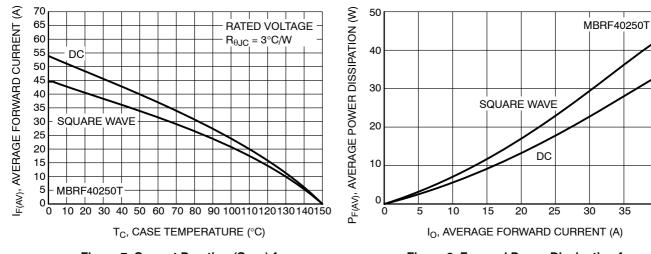
1. Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

IF INSTANTANEOUS FORWARD CURRENT (A) 100 100 IF, MAXIMUM FORWARD CURRENT (A) T_J = 150°C <u>T_J</u> = 150°C $T_J = 125^{\circ}C$ 10 10 $T_J = 100^{\circ}C$ = 100°C Т.і $T_{J} = 125^{\circ}C$ $T_J = 25^{\circ}C$ T_J = 25°C 1 0.8 0.3 0.4 0.5 0.6 0.7 0.9 1.0 0.3 0.4 0.5 0.6 0.7 0.8 0.9 1.0 1.1 V_F, INSTANTANEOUS FORWARD VOLTAGE (V) VE MAXIMUM FORWARD VOLTAGE (V) Figure 1. Typical Forward Voltage Figure 2. Maximum Forward Voltage 1.0E-01 700 $T_J = 25^{\circ}C$ €^{1.0E-02} 600 = 150°C ТJ 005 (pF) 007 /) LOE-03 0.0E-04 0.0E-05 0.0E-05 0.0E-05 0.0E-06 T_J = 125°C $T_J = 100^{\circ}C$ Ú 100 T_J = 25°C 1.0E-07 L 25 0 50 75 100 125 150 175 200 225 250 1 10 100 V_R, REVERSE VOLTAGE (V) V_R, REVERSE VOLTAGE (V) Figure 3. Typical Reverse Current Figure 4. Typical Capacitance $\mathsf{P}_{\mathsf{F}(\mathsf{AU})}, \mathsf{AVERAGE}$ POWER DISSIPATION (W) F(AV), AVERAGE FORWARD CURRENT (A) 70 50 65 DC RATED VOLTAGE MBR40250 60 MBR40250T $R_{\theta JC} = 2^{\circ}C/W$ 40 55 MBRB40250T 50 45 30 40 SQUARE WAVE SQUARE WAVE 35 30 20 25 20 DC 15 10 MBR40250 10 MBR40250T 5 MBRB40250 °∟ 0 10 20 30 40 50 60 70 80 90 100110120130140150 ō 5 10 15 20 25 30 35 40 T_C, CASE TEMPERATURE (°C) IO, AVERAGE FORWARD CURRENT (A) Figure 5. Current Derating (Case) for

TYPICAL CHARACTERISTICS

Figure 6. Forward Power Dissipation for MBR40250, MBR40250T and MBRB40250T

MBR40250, MBR40250T and MBRB40250T



TYPICAL CHARACTERISTICS

Figure 7. Current Derating (Case) for **MBRF40250T**

Figure 8. Forward Power Dissipation for **MBRF40250T**

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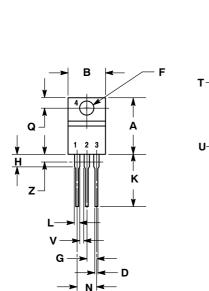
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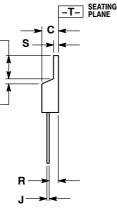
ORDERING INFORMATION

Device	Package	Shipping [†]
MBR40250	TO-220AC	
MBR40250G	TO-220AC (Pb-Free)	50 Units / Rail
MBR40250T	TO-220AB	
MBR40250TG	TO-220AB (Pb-Free)	50 Units / Rail
MBRF40250T	TO-220 FULLPACK	
MBRF40250TG	TO-220 FULLPACK (Pb-Free)	50 Units / Rail
MBRB40250TG	D ² PAK (Pb–Free)	50 Units / Rail
MBRB40250TT4G	D ² PAK (Pb-Free)	800 Units / Tape & Reel

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AF**



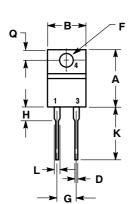


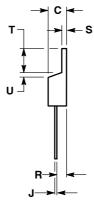
NOTES:

NUTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. DIMENSION 2 DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

MIN 0.570 0.380	MAX 0.620	MIN	MAX	
0.380		44.40		
		14.48	15.75	
	0.405	9.66	10.28	
0.160	0.190	4.07	4.82	
0.025	0.035	0.64	0.88	
0.142	0.161	3.61	4.09	
0.095	0.105	2.42	2.66	
0.110	0.155	2.80	3.93	
0.014	0.025	0.36	0.64	
0.500	0.562	12.70	14.27	
0.045	0.060	1.15	1.52	
0.190	0.210	4.83	5.33	
0.100	0.120	2.54	3.04	
0.080	0.110	2.04	2.79	
0.045	0.055	1.15	1.39	
0.235	0.255	5.97	6.47	
0.000	0.050	0.00	1.27	
0.045		1.15		
Z 0.080 2.04				
STYLE 6: PIN 1. ANODE 2. CATHODE 3. ANODE				
	0.110 0.014 0.500 0.045 0.190 0.045 0.235 0.000 0.045 6: 1. ANO 2. CATI 3. ANO	0.110 0.155 0.014 0.025 0.500 0.562 0.45 0.060 0.190 0.210 0.100 0.120 0.080 0.110 0.045 0.055 0.023 0.255 0.000 0.050 0.045 0.080 6: 1. ANODE 2. CATHODE 3. ANODE	0.110 0.155 2.80 0.014 0.025 0.36 0.500 0.562 12.70 0.045 0.600 1.15 0.190 0.210 4.83 0.100 0.120 2.54 0.080 0.110 2.04 0.080 0.110 2.04 0.080 0.110 2.04 0.045 0.055 1.15 0.235 0.255 5.97 0.000 0.050 0.00 0.045 1.15 0.080 6: 1. ANODE 2.<	

TO-220AC CASE 221B-04 ISSUE E





1	NOTES:
	1. DIMENSIONING AND TOLERANCING PER ANSI
	Y14 5M 1982

2. CONTROLLING DIMENSION: INCH. INCHES MILLIMETERS DIM MIN MAX MIN MAX
 A
 0.595
 0.620
 15.11
 15.75

 B
 0.380
 0.405
 9.65
 10.29
9.65 10.29 **C** 0.160 0.190 4.06 4.82 D 0.025 0.035 F 0.142 0.161 0.64 0.89 3.61 4.09
 G
 0.190
 0.210

 H
 0.110
 0.130
4.83 5.33 3.30 2.79 J 0.014 0.025 0.36 0.64
 K
 0.500
 0.562
 12.70
 14.27

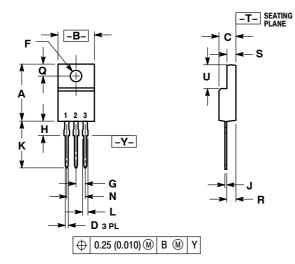
 L
 0.045
 0.060
 1.14
 1.52
Q 0.100 0.120 2.54 3.04
 R
 0.080
 0.110
 2.04
 2.79

 S
 0.045
 0.055
 1.14
 1.39

 T
 0.235
 0.255
 5.97
 6.48
U 0.000 0.050 0.000 1.27

PACKAGE DIMENSIONS

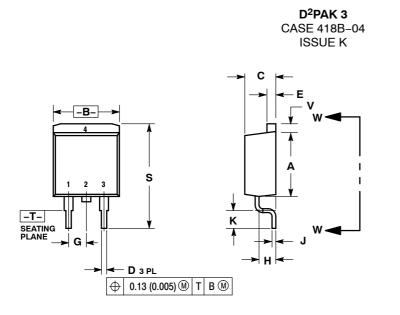
TO-220 FULLPAK CASE 221D-03 ISSUE J



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH 3. 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.617	0.635	15.67	16.12
В	0.392	0.419	9.96	10.63
C	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100 BSC		2.54 BSC	
Н	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
Ν	0.200 BSC		5.08 BSC	
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88

PACKAGE DIMENSIONS



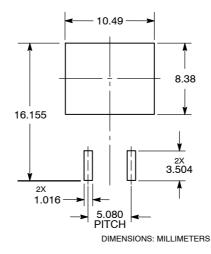
NOTES: 1. DIMENSIONING AND TOLERANCING DED ANSI VIA 5M 1000

PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. 418B-01 THRU 418B-03 OBSOLETE.

418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

	INCHES		MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.340	0.380	8.64	9.65
В	0.380	0.405	9.65	10.29
С	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
Е	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
н	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
κ	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
М	0.280	0.320	7.11	8.13
Ν	0.197 REF 5.00 REF		REF	
Р	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
۷	0.045	0.055	1.14	1.40

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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